

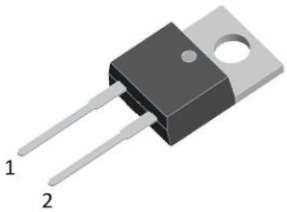
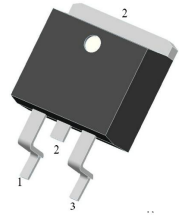
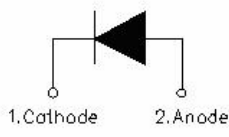
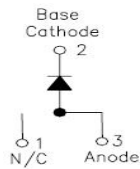
12TQ080/S 12TQ100/S SCHOTTKY RECTIFIER

Features

- 175°C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection

12TQ...	12TQ...S
	
	
TO-220AC	D ² PAK

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	80	12TQ080	V
Working Peak Reverse Voltage	V _{RWM}		100	12TQ100	
DC Blocking Voltage	V _R				
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _c =116°C, rectangular wave form	15		A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	276		A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.76	0.84	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.56	0.68	V
Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.003	0.55	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	0.02	7	mA
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	400	500	pF
Series Inductance	L _S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

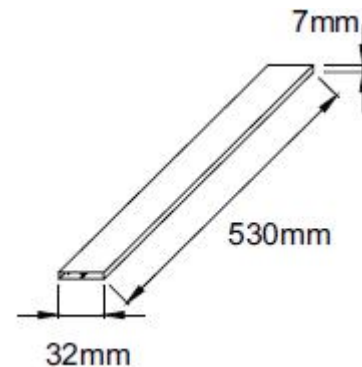
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	2.0	°C/W
Typical Thermal Resistance Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased(only for TO-220)	0.50	°C/W
Case Style	TO-220AC D ² PAK			

Tube Specification

Device	Package	Weight	Shipping
12TQ...	TO-220AC	1.8g	50pcs / tube
12TQ...S	D ² PAK	1.85g	800pcs / reel

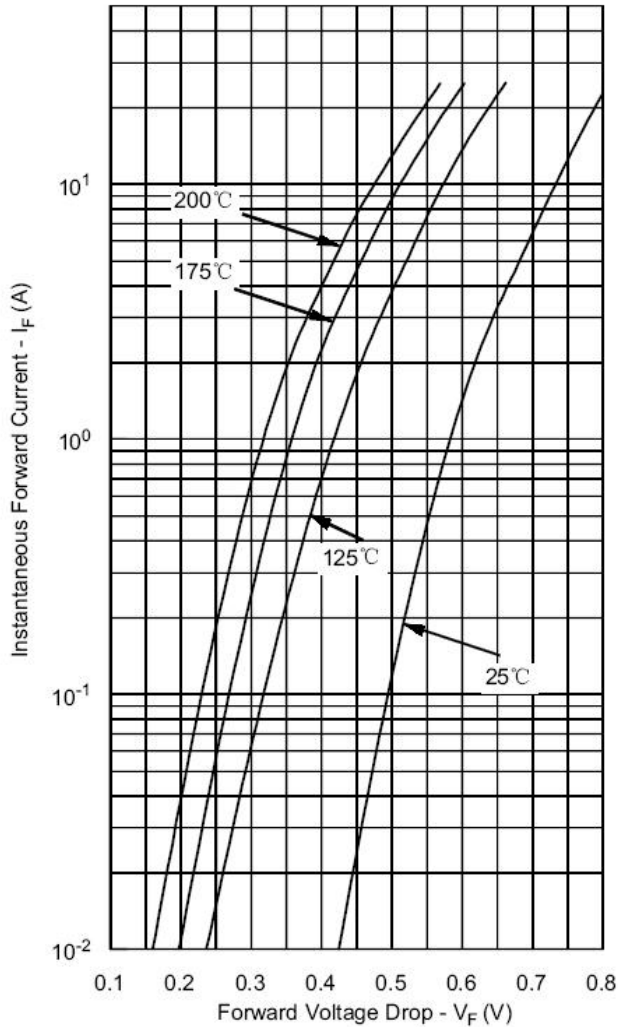
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification(TO-220AC)

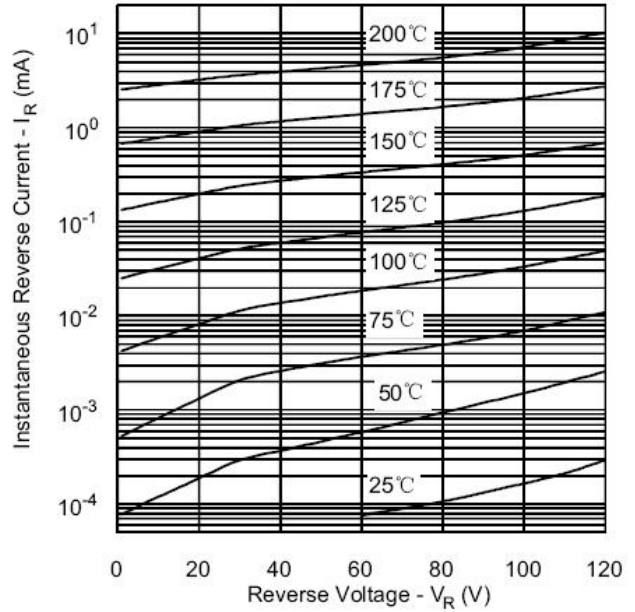


Ratings and Characteristics Curves

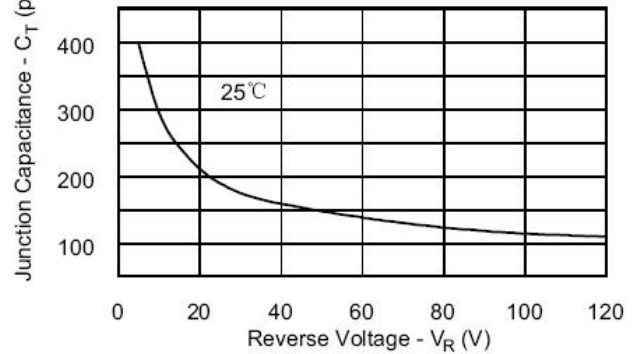
Typical Forward Characteristics



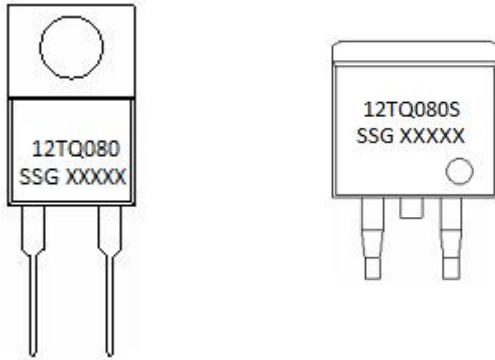
Typical Reverse Characteristics



Typical Junction Capacitance



Marking Diagram

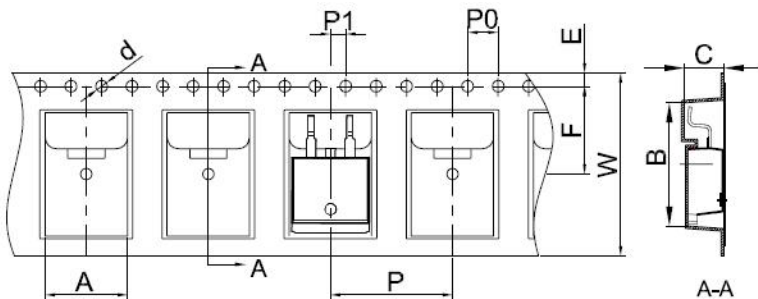


Where XXXXX is YYWWL

12 = Forward Current (12A)
 TQ = Device Type
 80/100 = Reverse Voltage (80/100V)
 S = Package type
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

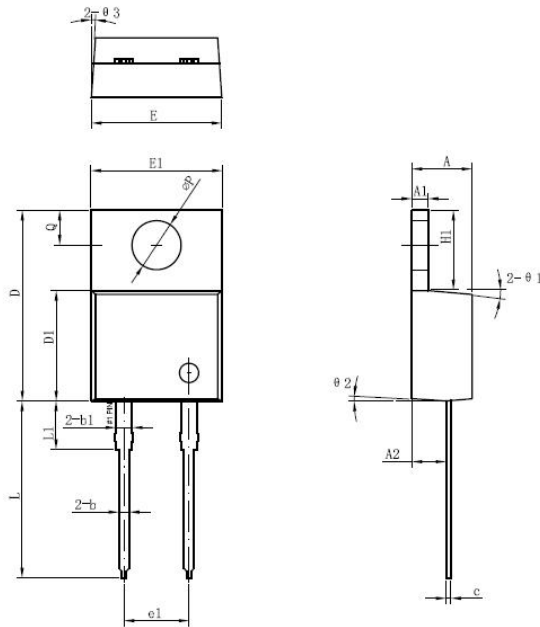
Cautions: Molding resin
 Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



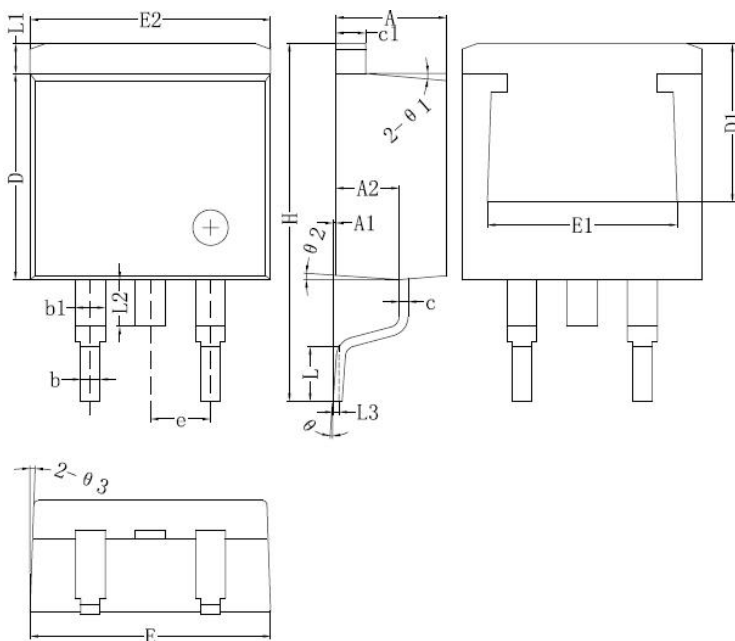
Symbol	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

Mechanical Dimensions TO-220AC



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
D	14.64	14.94	15.24
D1	8.50	8.07	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1	4.98	5.08	5.18
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1	3.56	3.80	3.96
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

Mechanical Dimensions D²PAK



Symbol	Millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

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